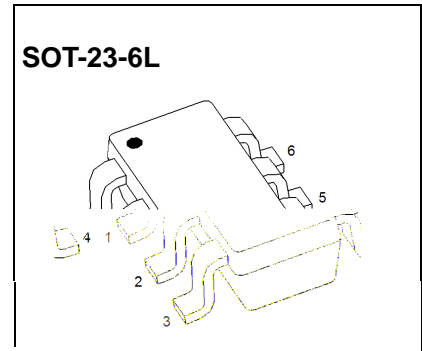




# SOT-23-6L Plastic-Encapsulate

## CJL2623 Dual P-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	$I_D$
-30V	130mΩ@-10V	-3A
	180mΩ@-4.5V	



### FEATURE

- ' TrenchFET Power MOSFET
- ' Low Gate Charge
- ' Low On-resistance
- ' Surface Mount Package

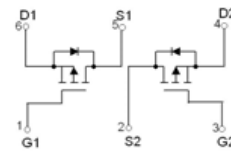
### APPLICATION

- ' DC/DC converter
- ' Load switch for portable devices
- ' Commercial-industrial applications

### MARKING:



### Equivalent Circuit



### ABSOLUTE MAXIMUM RATINGS ( $T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	-3	A
Pulsed Drain Current (note 1)	$I_{DM}$	-20	A
Power Dissipation (note 2)	$P_D$	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^{\circ}C/W$
Junction Temperature	$T_J$	150	$^{\circ}C$
Storage Temperature	$T_{STG}$	-55~ 150	$^{\circ}C$

- Notes :**
1. Pulse width limited by Max.junction temperature.
  2. Per element must not be exceeded

## MOSFET ELECTRICAL CHARACTERISTICS

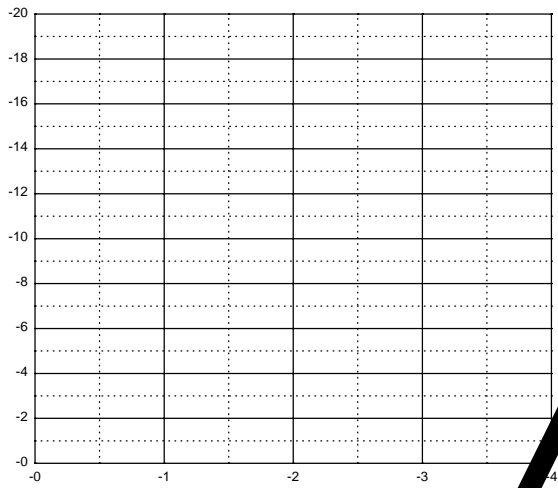
$T_a=25^\circ\text{C}$  unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>STATIC PARAMETERS</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = -30V, V_{GS} = 0V$			-1	$\mu A$
Gate-body leakage current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1		-3	V
Drain-source on-resistance (note 3)	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -3A$			130	$m\Omega$
		$V_{GS} = -4.5V, I_D = -2A$			180	$m\Omega$
Forward tranconductance	$g_{FS}$	$V_{DS} = -5V, I_D = -2A$		2		S
Diode forward voltage (note 3)	$V_{SD}$	$I_S = -1A, V_{GS} = 0V$			-1.2	V
<b>DYNAMIC PARAMETERS</b> (note 4)						
Input Capacitance	$C_{iss}$	$V_{DS} = -25V, V_{GS} = 0V, f = 1MHz$			240	pF
Output Capacitance	$C_{oss}$			42		pF
Reverse Transfer Capacitance	$C_{rss}$			32		pF
<b>SWITCHING PARAMETERS</b> (note 3,4)						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -15V, V_{GS} = -10V, I_D = -1A$ $R_D = 15\Omega, R_G = 3.3\Omega$		5		ns
Turn-on rise time	$t_r$			6		ns
Turn-off delay time	$t_{d(off)}$			15		ns
Turn-off fall time	$t_f$			3		ns
Total Gate Charge	$Q_g$				4.5	nC
$V_{DS} = -24V, V_{GS} = -4.5V, I_D = -2A$						

---

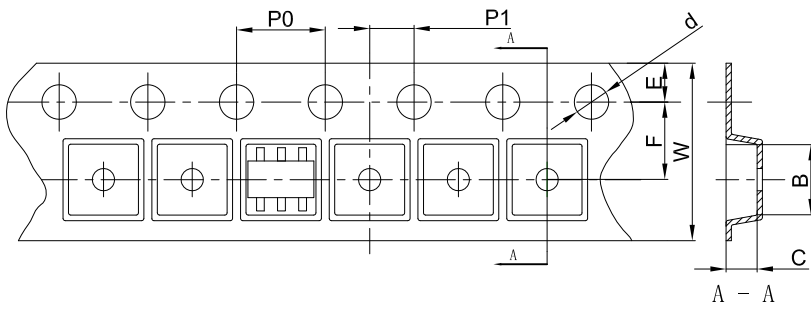
## Typical Characteristics

---



JCET reserve the right to make modifications.

NOTICE



**Packaging Description:**

SOT-23-6L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3